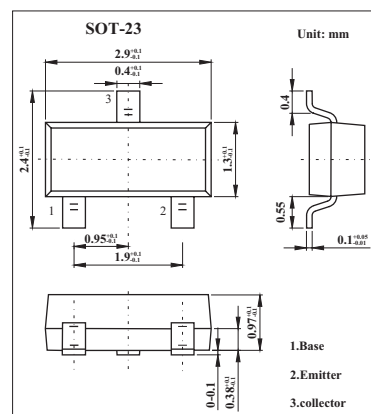


Silicon PNP Epitaxial

2SA1617

■ Features

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-55	V
Collector-emitter voltage	V_{CE0}	-50	V
Emitter-base voltage	V_{EB0}	-5	V
Collector current	I_C	-100	mA
Collector dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}$, $I_E = 0$	-55			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}$, $R_{BE} = \infty$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}$, $I_C = 0$	-5			V
Collector cutoff current	I_{CBO}	$V_{CB} = -30\text{V}$, $I_E = 0$			-0.5	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -2\text{V}$, $I_C = 0$			-0.5	μA
DC current gain	h_{FE}	$V_{CE} = -12\text{V}$, $I_C = -2\text{mA}$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\text{mA}$, $I_B = -1\text{mA}$			-0.2	V
Base-emitter voltage	V_{BE}	$V_{CE} = -12\text{V}$, $I_C = -2\text{mA}$			-0.8	V

■ h_{FE} Classification

Marking	VI	
Rank	B	C
h_{FE}	100~200	160~320